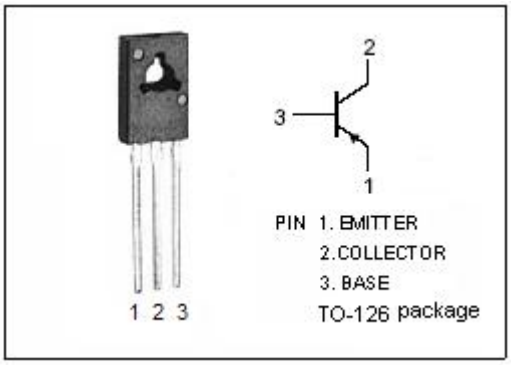
isc Silicon PNP Power Transistor 2SA738

DESCRIPTION

- Collector-Emitter Breakdown Voltage-
  $V_{(BR)CEO}$= -25V (Min)
- Good Linearity of h_{FE}
- Complement to Type 2SC1368
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

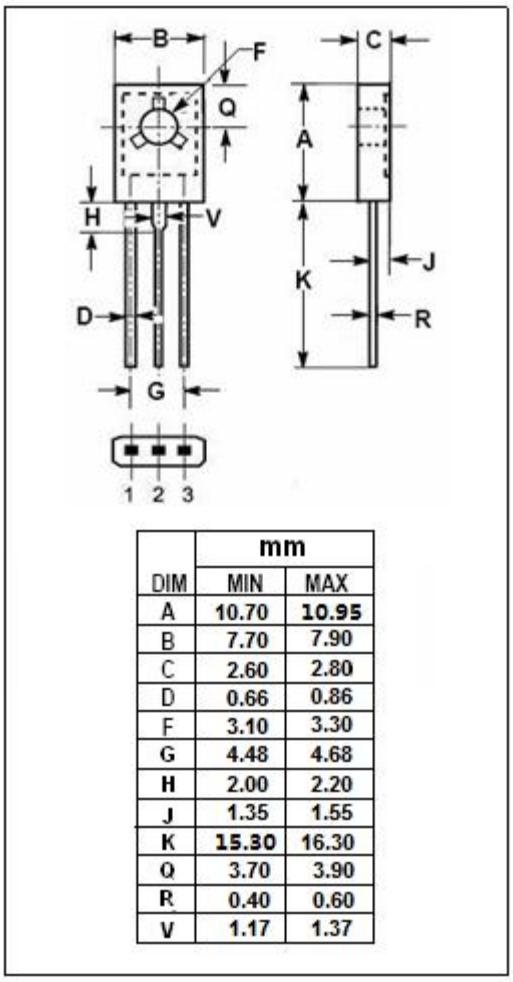


APPLICATIONS

- Designed for use as driver stages in high-fidelity amplifiers and TV circuits.

ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-25	V
V_{CEO}	Collector-Emitter Voltage	-25	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current-Continuous	-2.5	A
I_{CM}	Collector Current-Peak	-3.0	A
P_C	Total Power Dissipation @ T_C=25℃	8	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃



DIM	mm MIN	MAX
A	10.70	10.95
B	7.70	7.90
C	2.60	2.80
D	0.66	0.86
F	3.10	3.30
G	4.48	4.68
H	2.00	2.20
J	1.35	1.55
K	15.30	16.30
Q	3.70	3.90
R	0.40	0.60
V	1.17	1.37

isc Silicon PNP Power Transistor 2SA738

ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= -10mA; I_B= 0	-25			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= -500mA; I_B= -50mA			-0.5	V
$V_{BE(on)}$	Base-Emitter On Voltage	I_C= -500mA; V_{CE}= -2V			-1.0	V
I_{CBO}	Collector Cutoff Current	V_{CB}= -25V; I_E= 0			-1.0	μA
I_{EBO}	Emitter Cutoff Current	V_{EB}= -5V; I_C= 0			-1.0	μA
h_{FE}	DC Current Gain	I_C= -500mA; V_{CE}= -2V	60		320	
f_T	Current-Gain—Bandwidth Product	I_C= -50mA; V_{CE}= -5V		160		MHz